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C. Amendments to the Claims.

1. (Currently Amended) A memory cell, comprising:

a first node for storing a first potential;

a second node for storing a second potential;

transistor gates electrodes formed from a gate layer; anda capacitor having plates coupled between the first node and second node, a portion of one plate of the capacitor comprising a first interconnect wiring layer pattern, formed over the gate layer, that

includes a plurality of conductive layers and that electrically interconnects circuit devices of the memory cell.

2. (Original) The memory cell of claim 1, further comprising:

a first inverter having an input coupled to the first node and an output coupled to the second node; and

a second inverter having an input coupled to the second node and an output coupled to the first node; wherein

the first node stores a true data value and the second node stores a complementary data value.

3. (Original) The memory cell of claim 1, further including:

a first access transistor coupled to the first node; and

a second access transistor coupled to the second node.

4. (Cancelled)

5. (Currently Amended) The memory cell of claim 1, wherein:

the first interconnect wiring layer pattern includes a plurality of separate portions, each portion including bottom conductive layer, a dielectric layer formed over the bottom conductive layer, and a top conductive layer formed over the dielectric layer, the ~~top~~bottom conductive layer forming at least a portion of a first plate of the capacitor.

APR 02 2007

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

6. (Currently Amended) The memory cell of claim 5, further including:

a second conductive interconnect wiring formed over the first
conductive interconnect wiring layer pattern that forms at least a portion
of a second plate of the capacitor.

7. (Previously Presented) The memory cell of claim 6, wherein:

the second conductive interconnect wiring comprises titanium;
the bottom conductive layer comprises titanium nitride; and
the top conductive layer comprises titanium.

Claims 8 to 20 (Cancelled)

21. (Previously Presented) The memory cell of claim 1, wherein:

the gate layer is not in physical contact with a drain of any
transistor of the memory cell.

22. (Currently Amended) The memory cell of claim 1, wherein:

a first interconnect wiring that includes the first interconnect
wiring layer pattern,

a first portion of the first interconnect wiring is in physical contact
with the drains of a first and second transistor of the memory cell; and
a second portion of the first interconnect wiring, separate from the
first portion, is in physical contact with the drains of a third and fourth
transistor of the memory cell.

23. (Currently Amended) A memory cell, comprising:

a first data storage node;
a second data storage node; and
a capacitor comprising a first plate coupled to the first data storage
node, a second plate coupled to the second data storage node, and a

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

third plate separated from the first and second plates by a capacitor dielectric, the first and second plates comprising portions of an interconnect layer that electrically connects terminals of transistors of the memory cell to one another.

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